Amendments to the Claims

Pursuant to 37 C.F.R. 1.121, please amend the claims as follows:

1-24. (Withdrawn)

25-49. (Canceled)

50. (Previously presented) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

51. (Previously presented) A method of manufacturing a device according to claim 50, wherein the electrode is an anode or a cathode.

52. (Previously presented) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the anode, the wiring line and the interlayer insulating film;

forming a film for preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

53. (Previously presented) A method of manufacturing a device according to claim 52, wherein the electrode is an anode or a cathode.

54. (Previously presented) A method of manufacturing a device according to claim 52, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkylmonoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

55. (Previously presented) A method of manufacturing a device according to claim 54, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material is formed by spin coating or evaporation.

56. (Previously presented) A method of manufacturing a device according to claim 52, wherein the film for preventing the substrate from contamination and electrostatic discharge damage comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

57. (Previously presented) A method of manufacturing a device according to claim 53, wherein the method further comprises the steps of removing the film, etching the resin insulating film to form a bank, wiping the anode, forming an organic compound layer over the bank and the anode.

58. (Currently amended) A method of manufacturing a light emitting device comprising the steps of:

removing an anti-electrostatic film formed on a resin insulating film, the resin insulating film formed over a thin film transistor and anode;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the anode;

forming a cathode on the organic compound layer.

59. (Currently amended) A method of manufacturing a light emitting device according to claim 58, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl

sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzyla mmonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether,

60. Previously presented) A method of manufacturing a device according to claim 59, wherein the organic conductive material is formed by spin coating or evaporation.

61. (Original) A method of manufacturing a device according to claim 58, wherein the anti-electrostatic film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

62. (Previously presented) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a

first processing room to a second processing room.

63. (Previously presented) A method of manufacturing a light emitting device according to claim 62, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzyla mmonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

64. (Previously presented) A method of manufacturing a light emitting device according to claim 62, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

65. (Previously presented) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a first electrode over the interlayer insulating film;

forming a wiring line connecting to the first electrode over the interlayer insulating film;

forming a resin insulating film over the first electrode, the wiring line and

the interlayer insulating film;

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

66. (Previously presented) A method of manufacturing a light emitting device according to claim 65, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzyla mmonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

67. (Previously presented) A method of manufacturing a light emitting device according to claim 65, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

68. (Currently amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode over the interlayer insulating film;

forming a resin insulating film over the anode, the wiring line and the interlayer insulating film;

after forming the resin insulating film over the anode, the wiring line and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

69. (Previously presented) A method of manufacturing a light emitting device according to claim 68, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,

a lkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzyla mmonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

70. (Currently amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

after forming the resin insulating film over the electrode, the wiring line and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

71. (Previously presented) A method of manufacturing a light emitting device according to claim 70, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,

alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzyla mmonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

72. (Currently amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a first electrode over the interlayer insulating film;

forming a wiring line connecting to the first electrode over the interlayer insulating film;

forming a resin insulating film over the first electrode, the wiring line and the interlayer insulating film;

after forming the resin insulating film over the first electrode, the wiring line and the interlayer insulating film, forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

73. (Previously presented) A method of manufacturing a light emitting device according to claim 72, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

74. (Previously presented) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode over the interlayer insulating film;

forming a resin insulating film over the anode, the wiring line and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

75. (Previously presented) A method of manufacturing a light emitting device according to claim 74, wherein the organic insulating material is

selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

76. (Previously presented) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

77. (Previously presented) A method of manufacturing a light emitting device according to claim 76, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

78. (Previously presented) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a first electrode over the interlayer insulating film;

forming a wiring line connecting to the first electrode over the interlayer insulating film;

forming a resin insulating film over the first electrode, the wiring line and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

79. (Previously presented) A method of manufacturing a light emitting device according to claim 78, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

80. Previously presented) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

performing plasma treatment on a surface of the interlayer insulating film;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

81. (Previously presented) A method of manufacturing a light emitting device according to claim 80, wherein the film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,
a lkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzyla mmonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

82. (Previously presented) A method of manufacturing a light emitting device according to claim 80, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.